

Data Sheet Issue:- 2

Rectifier Diode Types W5838Z#180 to W5838Z#220 Previous Type No.: SW12-22#XC26C

Absolute Maximum Ratings

	VOLTAGE RATINGS	MAXIMUM LIMITS	UNITS
V _{RRM}	Repetitive peak reverse voltage, (note 1)	1800-2200	V
Vrsm	Non-repetitive peak reverse voltage, (note 1)	1900-2300	V

	OTHER RATINGS	MAXIMUM LIMITS	UNITS
IF(AV)M	Maximum average forward current, T _{sink} =55°C, (note 2)	5838	А
IF(AV)M	Maximum average forward current. T _{sink} =100°C, (note 2)	4296	А
IF(RMS)M	Nominal RMS forward current, T _{sink} =25°C, (note 2)	10560	А
I _{F(d.c.)}	D.C. forward current, T _{sink} =25°C, (note 3)	9206	А
IFSM	Peak non-repetitive surge t _p =10ms, V _{rm} =60%V _{RRM} , (note 4)	64.0	kA
IFSM2	Peak non-repetitive surge t _p =10ms, V _{rm} ≤10V, (note 4)	70.4	kA
l²t	I ² t capacity for fusing t_p =10ms, V_{rm} =60% V_{RRM} , (note 4)	20.5×10 ⁶	A ² s
l²t	I ² t capacity for fusing $t_p=10$ ms, $V_{rm} \le 10$ V, (note 4)	24.5×10 ⁶	A ² s
T _{j op}	Operating temperature range	-40 to +175	°C
T _{stg}	Storage temperature range	-40 to +175	°C

Notes:-

1) De-rating factor of 0.13% per °C is applicable for T_j below 25°C.

2) Double side cooled, single phase; 50Hz, 180° half-sinewave.

3) Double side cooled.

4) Half-sinewave, 175°C T_j initial.



Characteristics

	PARAMETER	MIN.	TYP.	MAX.	TEST CONDITIONS (Note 1)	UNITS
Vfm	Maximum peak forward voltage	-	-	1.3	IFM=6800A	V
V _{T0}	Threshold voltage	-	-	0.80		V
r⊤	Slope resistance	-	-	0.074		mΩ
I _{RRM}	Peak reverse current	-	-	100	Rated V _{RRM}	mA
D	Thermal registeres, junction to besteink	-	-	0.011	Double side cooled	K/W
RthJK	Thermal resistance, junction to heatsink	-	-	0.022	Single side cooled	K/W
F	Mounting force	27	-	47	Note 2	kN
Wt	Weight		1.7			kg

Notes:-

1) Unless otherwise indicated $T_j=175^{\circ}C$.

2) For other clamp forces, please consult factory.



 $W_{AV} = \frac{\Delta T}{R_{th}}$ $\Delta T = T_{j \max} - T_{K}$

Notes on Ratings and Characteristics

1.0 Voltage Grade Table

Voltage Grade	V _{RRM} V	V _{RSM} V	V _R DC V
18	1800	1900	1150
22	2200	2300	1350

2.0 Extension of Voltage Grades

This report is applicable to other voltage grades when supply has been agreed by Sales/Production.

3.0 De-rating Factor

A blocking voltage de-rating factor of 0.13%/°C is applicable to this device for T_j below 25°C.

4.0 Snubber Components

When selecting snubber components, care must be taken not to use excessively large values of snubber capacitor or excessively small values of snubber resistor. Such excessive component values may lead to device damage due to the large resultant values of snubber discharge current. If required, please consult the factory for assistance.

and:

5.0 Computer Modelling Parameters

5.1 Device Dissipation Calculations

$$I_{AV} = \frac{-V_{T0} + \sqrt{V_{T0}^{2} + 4 \cdot ff^{2} \cdot r_{T} \cdot W_{AV}}}{2 \cdot ff^{2} \cdot r_{T}}$$

Where $V_{T0}=0.80V$, $r_T=0.074m\Omega$,

 R_{th} = Supplementary thermal impedance, see table below and

ff = Form factor, see table below.

Supplementary Thermal Impedance						
Conduction Angle	6 phase (60°)	3 phase (120°)	½ wave (180°)	d.c.		
Square wave Double Side Cooled	0.0144	0.0132	0.0126	0.0116		
Square wave Cathode Side Cooled	0.0262	0.0251	0.0244	0.0235		
Sine wave Double Side Cooled	0.0133	0.0124	0.0115			
Sine wave Cathode Side Cooled	0.0253	0.0244	0.0234			

Form Factors						
Conduction Angle6 phase (60°)3 phase (120°)½ wave (180°)d.c.						
Square wave	2.449	1.732	1.414	1		
Sine wave	2.778	1.879	1.57			



5.2 Calculating VF using ABCD Coefficients

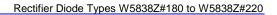
The on-state characteristic I_F vs. V_F, on page 8 is represented in two ways;

- (i) the well established V_{T0} and r_T tangent used for rating purposes and
- (ii) a set of constants A, B, C, D, forming the coefficients of the representative equation for V_F in terms of I_F given below:

$$V_F = A + B \cdot \ln(I_F) + C \cdot I_F + D \cdot \sqrt{I_F}$$

The constants, derived by curve fitting software, are given below for both hot and cold characteristics. The resulting values for V_F agree with the true device characteristic over a current range, which is limited to that plotted.

175°C Coefficients					
А	0.5234366				
B 4.457902×10 ⁻²					
С	7.774867×10 ⁻⁵				
D -1.697693×10 ⁻³					





5.3 D.C. Thermal Impedance Calculation

$$r_t = \sum_{p=1}^{p=n} r_p \cdot \left(1 - e^{\frac{-t}{\tau_p}}\right)$$

Where p = 1 to *n*, *n* is the number of terms in the series and:

- t = Duration of heating pulse in seconds.
- $r_t =$ Thermal resistance at time t.
- r_p = Amplitude of p_{th} term.
- τ_p = Time Constant of r_{th} term.

The coefficients for this device are shown in the tables below:

D.C. Double Side Cooled							
Term 1 2 3 4							
r _p	0.01551	2.7827×10 ⁻³	4.2105×10 ⁻³	0.9443×10 ⁻³			
τρ	10.04275	1.783567	0.2231307	3.428×10⁻³			

D.C. Double Side Cooled							
Term	Term 1 2 3 4 5						
rp	6.4176×10 ⁻³	2.7472×10 ⁻³	1.2515×10 ⁻³	0.6336×10⁻³	0.59597×10 ⁻³		
τρ	1.785337	0.34595	0.099651	0.014214	2.298151×10 ⁻³		



Curves

Max. forward dissipation (W)

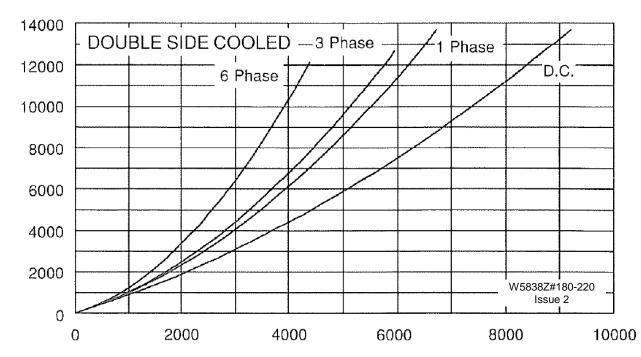
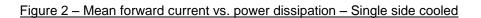
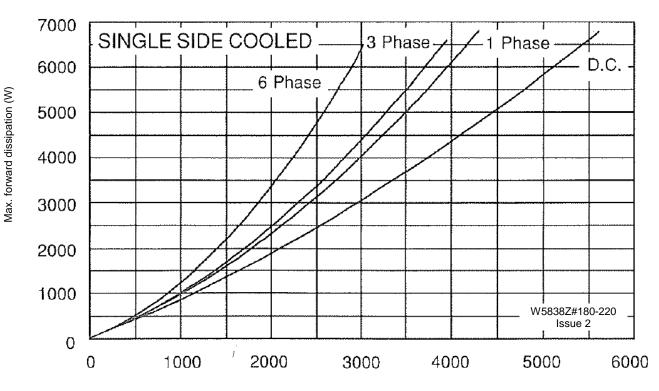


Figure 1 – Mean forward current vs. power dissipation- Double side cooled

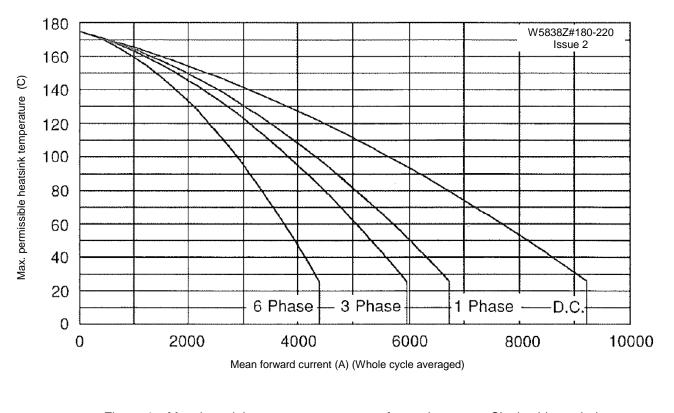
Mean forward current (A) (Whole cycle averaged)



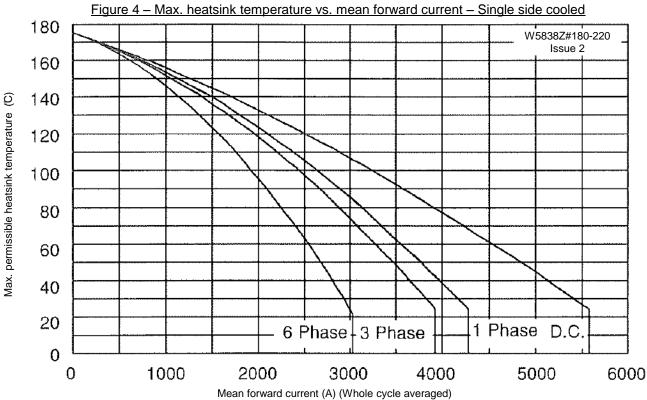


Mean forward current (A) (Whole cycle averaged)









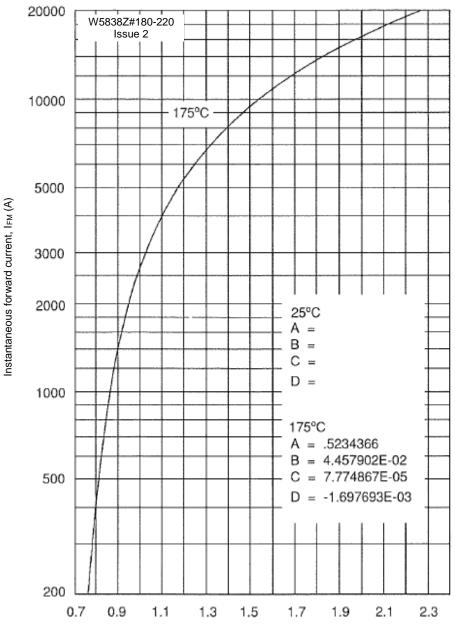


Figure 5 – Forward characteristics of limit device

Maximum instantaneous forward voltage, $V_{\mathsf{F}}\left(\mathsf{V}\right)$

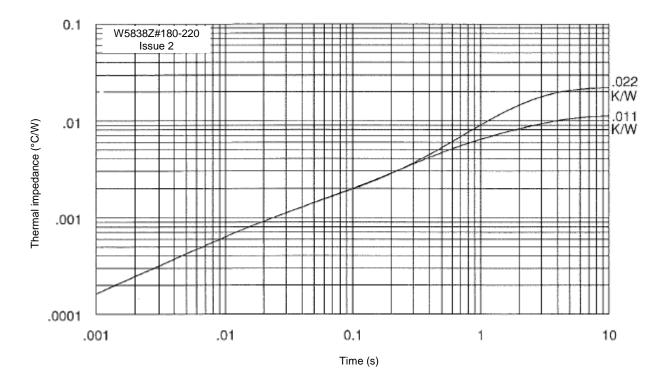


Figure 6 – Transient thermal impedance

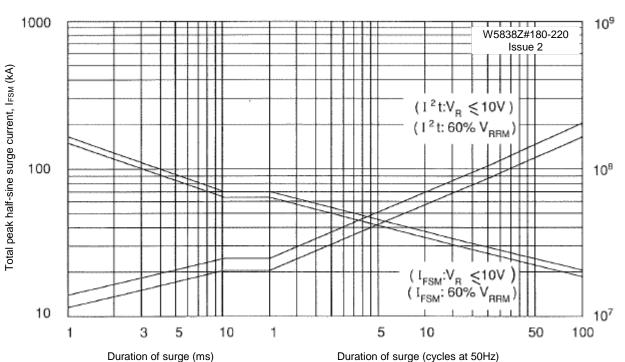


Figure 7 – Maximum non-repetitive surge current at initial junction temperature 175°C

IXYS



Outline Drawing & Ordering Information

